

# NTP90N02-VB Datasheet N-Channel 30-V (D-S) MOSFET

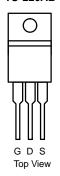
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0. 003				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0. 004				
I <sub>D</sub> (A)	120				
Configuration	Single				

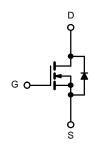
#### **FEATURES**

- Trench Power MOSFET
   100 % R<sub>g</sub> and UIS Tested
- Compliant to RoHS Directive 2011/65/EU



#### **TO-220AB**





N-Channel MOSFET

#### **APPLICATIONS**

- OR-ing
- Server
- DC/DC

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub> ± 20		v
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 25 °C		120	
	T <sub>C</sub> = 70 °C	L	60 <sup>e</sup>	A
	T <sub>A</sub> = 25 °C	I <sub>D</sub>	28.8 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C		19 <sup>b, c</sup>	^
Pulsed Drain Current	I <sub>DM</sub>	380		
Avalanche Current Pulse	e L = 0.1 mH		36	
Single Pulse Avalanche Energy	L = U.1 IIII	E <sub>AS</sub>	64.8	V
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	l.	90 <sup>a, e</sup>	^
	T <sub>A</sub> = 25 °C	I <sub>S</sub>	3.13 <sup>b, c</sup>	A
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		250 <sup>a</sup>	
	T <sub>C</sub> = 70 °C	P <sub>D</sub>	175	w
	T <sub>A</sub> = 25 °C	' D	3.75 <sup>b, c</sup>	¬
	T <sub>A</sub> = 70 °C		2.63 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Тур.	Max.	Unit		
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 10 sec	R <sub>thJA</sub>	32	40	°C/W		
Maximum Junction-to-Case	Steady State	R <sub>thJC</sub>	0.5	0.6	- 'C/VV		

- a. Based on T<sub>C</sub> = 25 °C.
  b. Surface mounted on 1" x 1" FR4 board.

- d. 1 = 10 sec.
   d. Maximum under steady state conditions is 90 °C/W.
   e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	1		Г		ı	_
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	30			V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 250 μA		35		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	_ ,		- 7.5		,
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	Inno	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Gurrent	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μΛ
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α
David Course Co. Olate Basistana 3	P	$V_{GS} = 10 \text{ V}, I_D = 28.8 \text{ A}$		0.003		Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 27 \text{ A}$		0.004		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 28.8 A		160		S
Dynamic <sup>b</sup>						•
Input Capacitance	C <sub>iss</sub>			3100		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		725		
Reverse Transfer Capacitance	C <sub>rss</sub>			370		
Total Cata Channa	0	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 28.8 \text{ A}$		171	257	nC
Total Gate Charge	$Q_g$			81.5	123	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 28.8 \text{ A}$		34		
Gate-Drain Charge	$Q_{gd}$			29		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			18	27	
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_{L} = 0.625 \Omega$		11	17	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong 24$ A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		70	105	
Fall Time	t <sub>f</sub>			10	15	
Turn-On Delay Time	t <sub>d(on)</sub>			55	83	
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_{L} = 0.67 \Omega$		180	270	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 22.5 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		55	83	
Fall Time	t <sub>f</sub>	- -		12	18	
Drain-Source Body Diode Characteristic	:S				ı	
Continuous Source-Drain Diode Current	Is	T <sub>C</sub> = 25 °C			90	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				90	A
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			52	78	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			70.2	105	nC
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		27		ns
Reverse Recovery Rise Time	t <sub>b</sub>			25		

#### Notes:

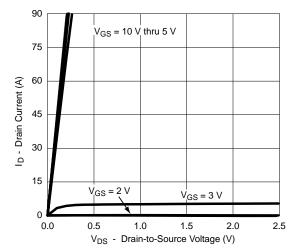
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

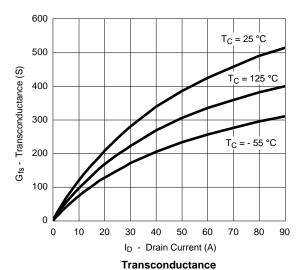
服务热线:400-655-8788

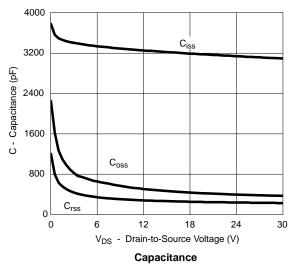


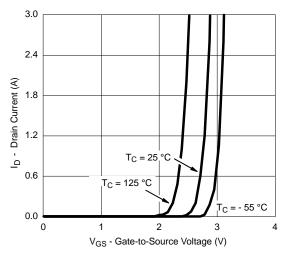
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



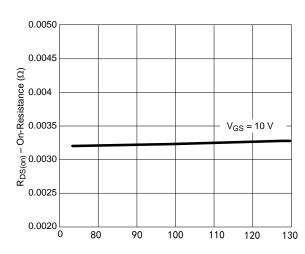
#### **Output Characteristics**



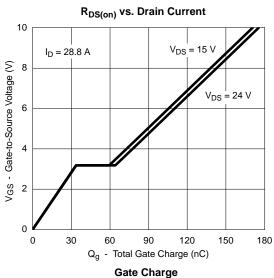




Transfer Characteristics



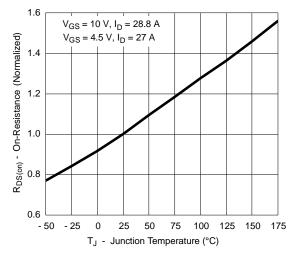
I<sub>D</sub> - Drain Current (A)



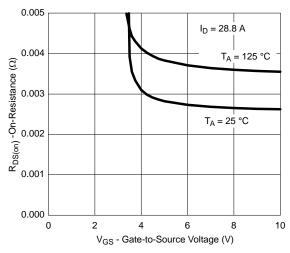
服务热线:400-655-8788



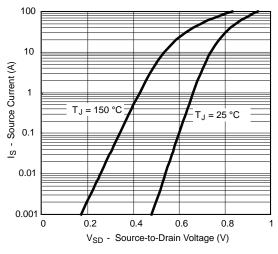
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



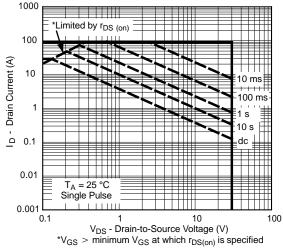
 $R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature



Forward Diode Voltage vs. Temperature



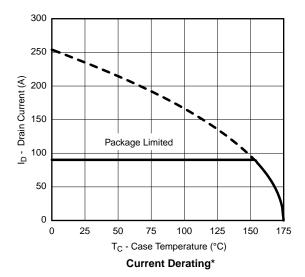
Threshold Voltage

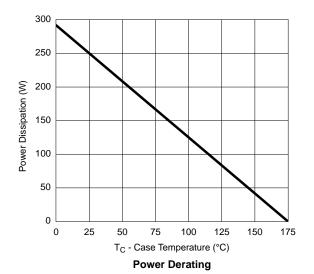


Safe Operating Area, Junction-to-Ambient

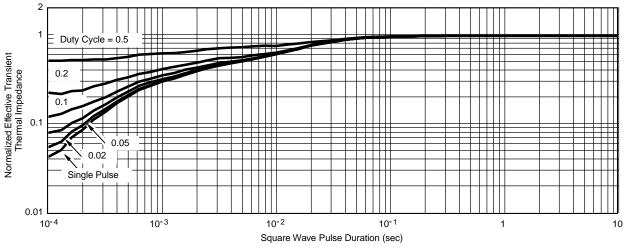


#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





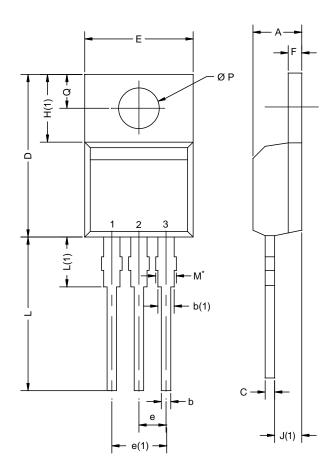
\*The power dissipation  $P_D$  is based on  $T_{J(max)}$  = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Normalized Thermal Transient Impedance, Junction-to-Case



## **TO-220AB**



	MILLIM	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

#### Notes

服务热线:400-655-8788

 $<sup>^{\</sup>star}$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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